

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-1880

Serial No. New Application

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Takashi INUSHIMA et al

Filing Date: November 10, 1998

Group: 1762

jc549 U.S. PAT. 09/188382 11/10/98

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
38	4,137,365	01/30/79	Wydeven et al	428	412	
	4,872,947	10/10/89	Wang et al	216	38	
	4,892,753	01/09/90	Wang et al	427	579	
	5,000,113	03/19/91	Wang et al	118	723	
	5,354,715	10/11/94	Wang et al	438	699	
	5,362,526	11/08/94	Wang et al	427	573	
	4,282,268	08/04/81	Priestley et al	427	579	06/06/78
	4,419,385	12/06/83	Peters	427	99	09/24/81
	4,567,352	01/28/86	Mimura et al	219	405	
	4,719,123	01/12/88	Haku et al	427	53.1	
	3,661,637	05/09/72	Sirtl	427	54.1	
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	3,026,435	03/20/62	McPherson	313	22	
	3,665,235	05/23/72	Hugot	313	24	
	4,323,810	04/06/82	Horstmann	313	24	
	3,619,682	11/09/71	Lo	313	22	
	3,372,672	03/12/68	Wright	427	54.1	
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	4,558,660	12/17/85	Nishizawa	118	715	
	4,612,207	09/16/86	Jansen	118	723	
	4,615,294	10/07/86	Scapple	118	725	
	4,676,195	06/30/87	Yasui	118	723	
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	4,532,022	07/30/85	Takashi et al	—	39	
	4,532,196	07/30/85	Yasui et al	—	39	
	4,539,068	09/03/85	Takugi et al	427	39	
Examiner <i>Passaio</i>	Date Considered <i>1-7-99</i>					

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	4,435,445	03/06/84	Allred et al	427	54.1	
	4,654,226	03/31/87	Jackson et al	427	54.1	
	4,726,963	02/23/88	Ishihara et al	427	53.1	06/09/87
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	4,544,423	10/01/85	Tsuge et al	427	74	02/10/84
	4,608,117	08/26/86	Ehrlich et al	427	53.1	06/01/82
	4,330,570	<i>5-22-88</i> 03/18/82	Giuliani et al	427	64	
	4,402,997	<i>9-20-83</i> 04/06/83	Hogan et al	118	71.5	
	4,695,331	09/21/87	Romaprasud	427	54.1	
	4,699,805	10/13/87	Seelbach et al	118	71.5	07/03/86
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	4,509,451	04/09/85	Collins et al	427	39	
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	3,228,812	01/11/66	Blake	427	93x	
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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
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	63-246829	10/13/88	Japan			Abstract	
	59-194452	11/05/84	Japan			Abstract	
	59-82732	05/12/84	Japan			Abstract	
	62-188375	08/17/87	Japan			Abstract	
	61-234531	10/18/86	Japan			Abstract	
	62-054940	03/10/87	Japan			Abstract	
	61-228633	10/11/86	Japan			Abstract	
	59-087834	05/21/84	Japan			Abstract	
	64-28925	01/31/89	Japan			Abstract	
	51-21753	07/05/76	Japan			Abstract	
	59-104120	1984	Japan				X
	61-103539	1986	Japan			Abstract	
	63-147314	1988	Japan				X
	61-063020	1986	Japan				X
	60-167318	08/30/85	Japan				X
	2-219232	08/31/90	Japan				X
	182797	09/06/66	USSR	313	22		X
	60-245217	05/12/85	Japan	—	—		X
	61-65419	04/04/86	Japan	118	725		X
	61-210622	09/18/86	Japan	118	725		X
	62-80272	04/13/87	Japan	118	725		X
	62-160462	07/16/87	Japan	118	725		X
	63-147314	06/20/88	Japan				X
	61-063020	04/01/86	Japan				X
	60-167318	08/30/85	Japan				X
	2-219232	08/31/90	Japan				X

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